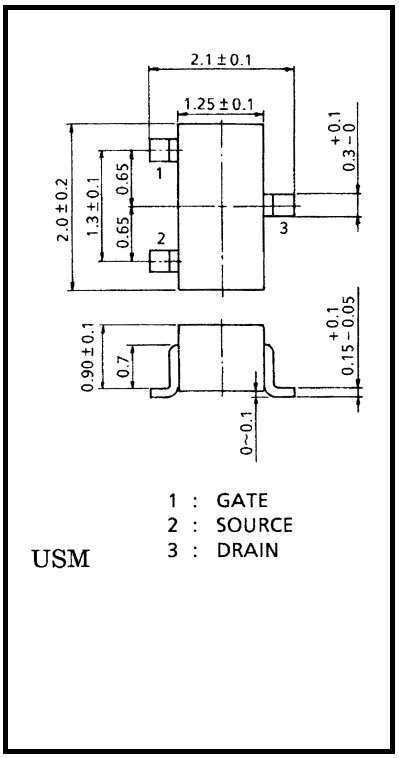
2SK2824

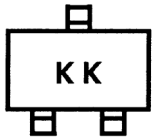
Analog Switch Applications

- High input impedance
- 1.5 V gate drive
- Low gate threshold voltage: V_{th} = 0.5~1.0 V
- Small package

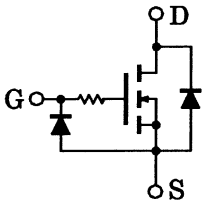


Weight: 0.006 g (typ.)

Marking



Equivalent Circuit



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GSS}	10	V
DC drain current	I_D	100	mA
Drain power dissipation	P_D	100	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: This transistor is electrostatic sensitive device.

Please handle with caution.

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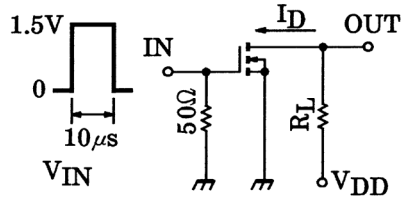
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = 10 V, V_{DS} = 0	—	—	1	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 100 μA, V_{GS} = 0	20	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = 20 V, V_{GS} = 0	—	—	1	μA
Gate threshold voltage		V_{th}	V_{DS} = 1.5 V, I_D = 0.1 mA	0.5	—	1.0	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 1.5 V, I_D = 10 mA	35	70	—	mS
Drain-source ON resistance 1		$R_{DS\ (ON)\ 1}$	I_D = 1 mA, V_{GS} = 1.2 V	—	15	50	Ω
Drain-source ON resistance 2		$R_{DS\ (ON)\ 2}$	I_D = 10 mA, V_{GS} = 1.5 V	—	10	40	Ω
Drain-source ON resistance 3		$R_{DS\ (ON)\ 3}$	I_D = 10 mA, V_{GS} = 2.5 V	—	7	28	Ω
Input capacitance		C_{iss}	V_{DS} = 1.5 V, V_{GS} = 0, f = 1 MHz	—	12	—	pF
Reverse transfer capacitance		C_{rss}	V_{DS} = 1.5 V, V_{GS} = 0, f = 1 MHz	—	3.4	—	pF
Output capacitance		C_{oss}	V_{DS} = 1.5 V, V_{GS} = 0, f = 1 MHz	—	12	—	pF
Switching time	Turn-on time	t_{on}	V_{DD} = 1.5 V, I_D = 10 mA, V_{GS} = 0~1.5 V	—	0.35	—	μs
	Turn-off time	t_{off}		—	0.2	—	

Switching Time Test Circuit

(1) Test circuit



V_{DD} = 1.5V
D.U. ≦ 1%
V_{IN} : t_r, t_f < 5ns
(Z_{out} = 50Ω)
COMMON SOURCE
Ta = 25°C

(2) V_{IN}
V_{GS}

(3) V_{OUT}
V_{DS}